

*Q3*  
*sub 4*  
19. (Amended) A method according to claim 18 wherein said channel region is substantially intrinsic type or p-type.

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*Q4*  
*sub 6*  
24. (Amended) A method according to claim 23 wherein said channel region is substantially intrinsic type or p-type.

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*Q5*  
*sub 9*  
30. (Amended) A method according to claim 23 wherein said channel region is substantially intrinsic type or p-type.

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*D6*  
*sub 1*  
53. (Amended) A method for fabricating a semiconductor device, said semiconductor device having at least one thin film transistor comprising a semiconductor film formed adjacent to a gate electrode with a gate insulating film therebetween, said method comprising the steps of:  
forming said semiconductor film over a substrate;  
forming an insulating film on said semiconductor film;  
introducing boron into at least a portion of said semiconductor film through said insulating film, said portion becoming at least a channel region of said thin film transistor; and  
removing said insulating film.

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Please add new claims 62-64 as follows:

*Q7*  
*D1*  
--62. A method according to claim 18 wherein said crystallizing said semiconductor film by laser irradiation is performed through said insulating film.

63. A method according to claim 23 wherein said crystallizing said semiconductor film by laser irradiation is performed through said insulating film.

64. A method according to claim 29 wherein said crystallizing said semiconductor film by laser irradiation is performed through said insulating film.--

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